

ABSTRACT OF THE DISCLOSURE

Two charge transfer passages of one TFT, which comprise two areas with island layers of p-Si intersecting at right angles and
5 running from respective drain areas ND, PD to source areas NS, PS through an LD area LD and a channel area CH, are arranged non-parallel to each other. Even if a defective crystallization area R, which is caused due to uneven intensity in an irradiated area in laser annealing for forming p-Si of a p-Si TFT LCD, passes across
10 the TFT area, and either of the transfer passages is defective, the remaining one operates normally, and the component characteristics are maintained as desired.